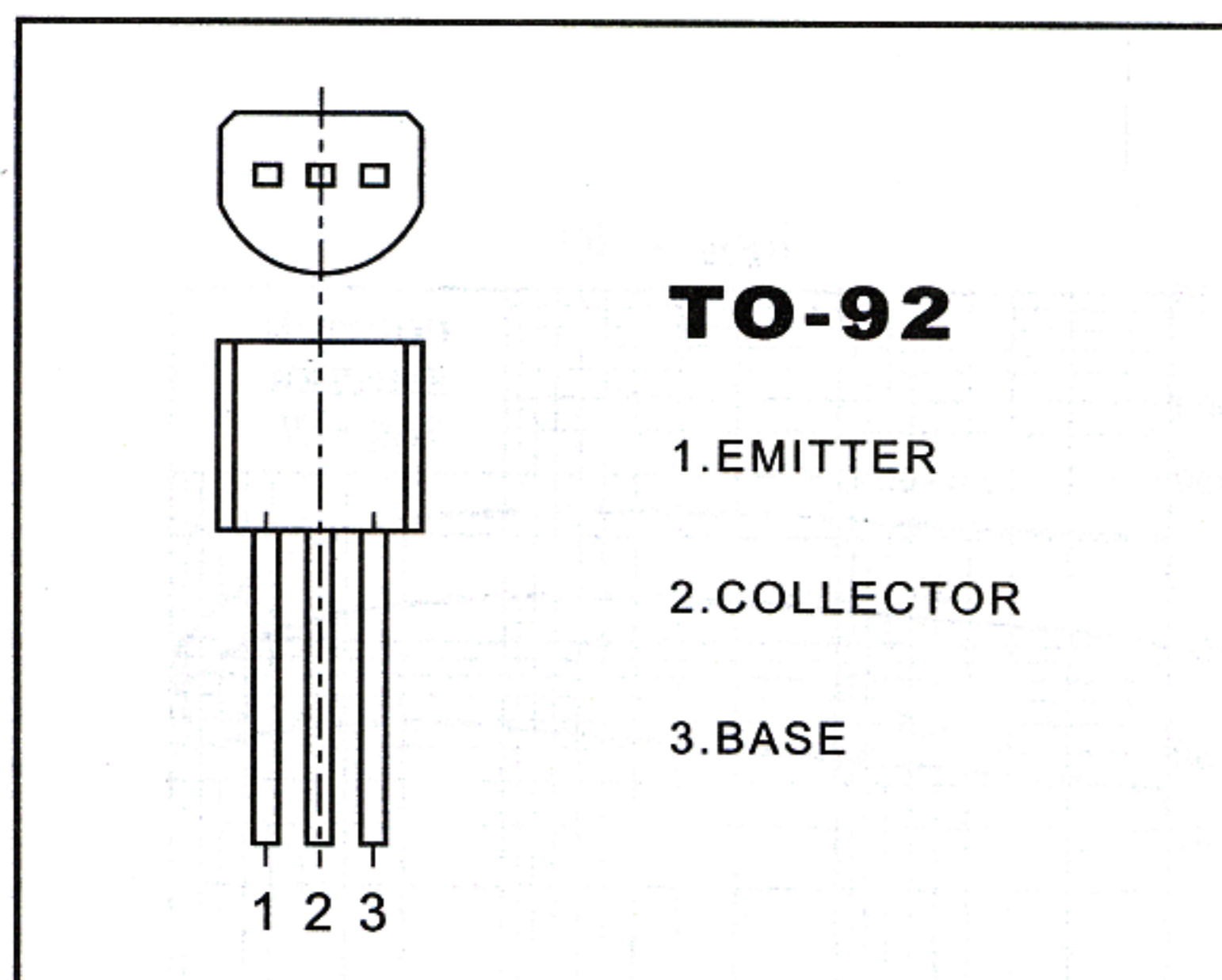


2SC2120 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.6W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.8 A

Collector-base voltage

$V_{(BR)CBO}$: 35 V

Operating and storage junction temperature range

T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

T_J : $150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1mA, I_E = 0$	35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1mA, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 35V, I_E = 0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 25V, I_B = 0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		0.1	μA
DC current gain	h_{FE}	$V_{CE} = 1V, I_C = 100mA$	100	320	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 500mA, I_B = 20mA$		0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1V, I_C = 10mA$		0.8	V
Transition frequency	f_T	$V_{CE} = 5V, I_C = 10mA$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320

